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#### SINGLE CHANNEL POWER DISTRIBUTION LOAD SWITCH

## **Description**

The AP22804/AP22814 is a single channel current-limited integrated high-side power switch optimized for Universal Serial Bus (USB) and other hot-swap applications. The family of devices complies with USB standards and is available with both polarities of Enable input.

The device has fast short-circuit response time for improved overall system robustness, and has an integrated output discharge function to ensure completely controlled discharging of the output voltage capacitor. They provide a complete protection solution for applications subject to heavy capacitive loads and the prospect of short circuit, and offer reverse current blocking, over-current, over-temperature and short-circuit protection, as well as controlled rise time and under-voltage lockout functionality. A 6ms deglitch capability on the open-drain Flag output prevents false over-current reporting and does not require any external components.

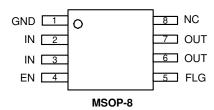
The AP22804/AP22814 is available in a standard Green SOT25, MSOP-8 and U-DFN2020-6 packages with exposed PAD for improve thermal performance and is RoHS compliant.

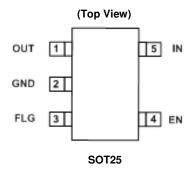
#### **Features**

- Input Voltage Range: 2.7V to 5.5V
- 50mΩ On-resistance
- Built-in Soft-start with 0.6ms Typical Rise Time
- Fault Report (FLG) with Blanking Time (6ms Typ)
- ESD Protection: 2kV HBM, 200V MM
- Active Low (B) or Active High (A) Enable
- Protection
  - Over Current with Auto Recovery
  - Short Circuit with Auto Recovery
  - Over Temperature with Auto Recovery
- Output Reverse Current / Voltage Protection
- Thermally Efficient Low Profile Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- UL Recognized, File Number E322375
- IEC60950-1 CB Scheme Certified

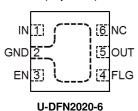
## **Pin Assignments**

## (Top View)





#### (Top View)



## **Applications**

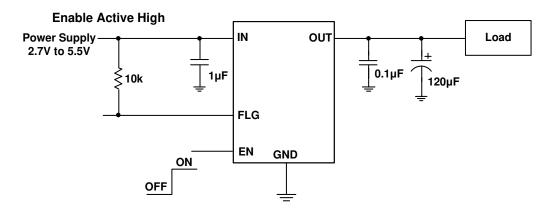
- Integrated Load Switches in Ultrabook PC's
- Power Up/Down Sequencing in Ultrabook PC's
- Notebook
- Netbook
- Set-Top Boxes
- SSD (Solid State Drives)
- Consumer Electronics
- Tablet PC
- Telecom Systems

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



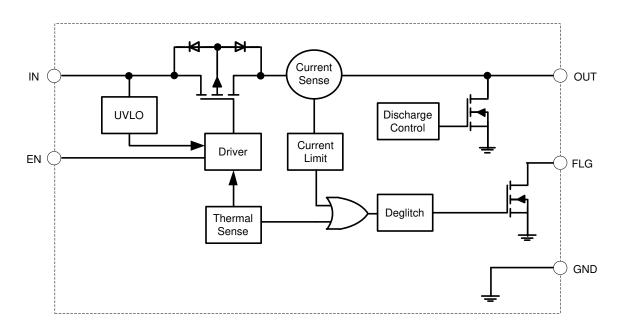
# **Typical Applications Circuit**



## **Pin Descriptions**

	Pin Number		Pin Name	Function
SOT25	U-DFN2020-6	MSOP-8	Pin Name	Function
1	5	6, 7	OUT	Voltage Output Pin, connect a 0.1µF bypass capacitor and a high-value capacitor to GND, close to IC. (At least 10µF in USB application.)
2	2	1	GND	Ground Pin of the Circuitry
3	4	5	FLG	Over Current and Over temperature fault report; Open-Drain flag is active low when triggered.
4	3	4	EN	Enable Input. Enable input, active high (A) or active low (B)
5	1	2, 3	IN	Voltage Input Pin, connect a 1µF low ESR capacitor to GND, close to IC.
_	6	8	NC	No Internal Connection
_	PAD	_	_	Recommend connecting to the GND externally for improved power dissipation

# **Functional Block Diagram**





# **Absolute Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.) (Note 4)

Symbol	Parameter	Ratings	Units		
ESD HBM	Human Body ESD Protection		2000	V	
ESD MM	Machine Model ESD Protection		200	V	
V <sub>IN</sub>	Input Voltage		-0.3 to 6.0	V	
V <sub>OUT</sub>	Output Voltage		-0.3 to (V <sub>IN</sub> + 0.3)	V	
V <sub>EN</sub>	Enable Voltage		-0.3 to (V <sub>IN</sub> + 0.3)	V	
ΙL	Load Current	Internal Limited	Α		
T <sub>J(max)</sub>	Maximum Junction Temperature	+150	°C		
T <sub>ST</sub>	Storage Temperature		-65 to +150	°C	
		MSOP-8	165		
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	SOT25	175	°C/W	
		U-DFN2020-6	100		
		MSOP-8	33		
$R_{\theta JC}$	Thermal Resistance, Junction to Case	SOT25	39	°C/W	
		U-DFN2020-6	20		

Note:

# **Recommended Operating Conditions (Note 5)**

Symbol	Parameter	Min	Max	Unit
V <sub>IN</sub>	Input Voltage	2.7	5.5	V
	Output Current (AP22804)	0	2.5	A
lout	Output Current (AP22814)	0	3.0	Α
$V_{IL}$	EN Input Logic Low Voltage	0	0.5	V
$V_{IH}$	EN Input Logic High Voltage	1.5	V <sub>IN</sub>	V
T <sub>A</sub>	Operating Ambient Temperature	-40	+85	°C

Note:

5. Refer to the typical application circuit.

<sup>4.</sup> Stresses greater than the 'Absolute Maximum Ratings' specified above may cause permanent damage to the device. These are stress ratings only; functional operation of the device at these or any other conditions exceeding those indicated in this specification is not implied. Device reliability may be affected by exposure to absolute maximum rating conditions for extended periods of time.

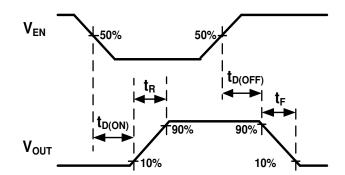


# $\hline \textbf{Electrical Characteristics} \ (V_{IN} = 5 \\ \hline V \ @ \ T_A = +25 \\ ^{\circ}C, \ C_{IN} = 1 \\ \mu F, \ C_L = 100 \\ n F, \ unless \ otherwise \ specified.)$

Symbol	Parameter	Test Conditions			Min	Тур	Max	Unit
$V_{UVLO}$	Input UVLO	V <sub>IN</sub> rising			1.6	2.0	2.4	٧
$\Delta V_{UVLO}$	Input UVLO Hysteresis	V <sub>IN</sub> decreasing			_	180	_	mV
I <sub>SHDN</sub>	Input Shutdown Current	Disabled, Ol	JT = open		_	0.1	1	μΑ
ΙQ	Input Quiescent Current	Enabled, OU	JT = open		_	80	_	μΑ
I <sub>LEAK</sub>	Input Leakage Current	Disabled, Ol	JT grounded		_	0.1	1	μΑ
I <sub>REV</sub>	Reverse Leakage Current	Disabled, V <sub>IN</sub>	$v = 0V$ , $V_{OUT} = 5V$ , $I_{REV}$ a	at V <sub>IN</sub>	_	0.01	1	μΑ
			V <sub>IN</sub> = 5.0V, I <sub>OUT</sub> = 1A	MSOP-8	_	50	65	
R <sub>DS(ON)</sub>	Switch On-Resistance	AP228X4	V <sub>IN</sub> = 5.0V, I <sub>OUT</sub> = 1A	SOT25	_	50	65	mΩ
			V <sub>IN</sub> = 5.0V, I <sub>OUT</sub> = 1A	U-DFN2020-6	_	50	65	
	Over Lead Overset Limit	AP22804, V <sub>I</sub>	<sub>N</sub> = 5V, V <sub>OUT</sub> = 4.5V	-	2.7	3.0	3.3	Α
I <sub>LIMIT</sub>	Over Load Current Limit	AP22814, V <sub>I</sub>	<sub>N</sub> = 5V, V <sub>OUT</sub> = 4.5V		3.1	3.45	3.8	Α
1	Short-Circuit Current Limit	AP22804, Er	nabled, Output short to g	round	_	0.45	_	Α
I <sub>SHORT</sub>	Short-Gircuit Gurrent Limit	AP22814, Er	nabled, Output short to g	round	_	0.65	_	Α
$V_{IL}$	EN Input Logic Low Voltage	$V_{IN} = 2.7V \text{ to}$	5.5V		_	_	0.65	V
$V_{IH}$	EN Input Logic High Voltage	$V_{IN} = 2.7V \text{ to}$	5.5V		1.5	_	_	٧
I <sub>LEAK-EN</sub>	EN Input Leakage	$V_{IN} = 5V, V_{EI}$	<sub>N</sub> = 0V and 5.5V		_	0.01	1	μΑ
I <sub>LEAK-O</sub>	Output Leakage Current	Disabled, V <sub>O</sub>	out = 0V		_	0.5	1	μΑ
t <sub>D(ON)</sub>	Output Turn-On Delay Time	$C_L = 4.7 \mu F$ , F	$R_{LOAD} = 10\Omega$ @ $V_{IN} = 3.3$	BV Figure 1	_	1.7	_	ms
t <sub>R</sub>	Output Turn-On Rise Time	$C_L = 4.7 \mu F, F$	$R_{LOAD} = 10\Omega @ V_{IN} = 3.3$	BV Figure 1	1.0	2.1	3.5	ms
t <sub>D(OFF)</sub>	Output Turn-Off Delay Time	$C_L = 4.7 \mu F, F$	$R_{LOAD} = 10\Omega @ V_{IN} = 3.3$	3V Figure 1	_	20	_	μs
t <sub>F</sub>	Output Turn-Off Fall Time	$C_L = 4.7 \mu F, F$	$R_{LOAD} = 100\Omega$ @ $V_{IN} = 3$	.3V Figure 1	_	0.65	_	ms
R <sub>FLG</sub>	FLG Output FET On-Resistance	I <sub>FLG</sub> = 10mA			_	40	60	Ω
I <sub>FOH</sub>	FLG Off Current	V <sub>FLG</sub> = 5V			_	0.01	1	μΑ
t <sub>BLANK</sub>	FLG Blanking Time	Assertion or temperature	deassertion due to overc	current and over-	2	6	13	ms
t <sub>DIS</sub>	Discharge Time	$C_L = 1 \mu F, V_{II}$	$_{N} = 5V$ , disabled to $V_{OUT}$	< 0.5V	_	0.4	_	ms
R <sub>DIS</sub>	Discharge Resistance	V <sub>IN</sub> = 5V, disabled, I <sub>OUT</sub> = 1mA		_	90	130	Ω	
T <sub>SHDN</sub>	Thermal Shutdown Threshold	Enabled		_	+140	_	°C	
T <sub>HYS</sub>	Thermal Shutdown Hysteresis	_			_	+35	_	°C
V <sub>RVP</sub>	Reverse-Voltage Comparator Trip Point	V <sub>OUT</sub> - V <sub>IN</sub>			25	50	75	mV
I <sub>ROCP</sub>	Reverse Current Limit	V <sub>OUT</sub> - V <sub>IN</sub> =	100mV		_	400	_	mA
†TRIG	Time from Reverse-Voltage Condition to MOSFET Turn Off	V <sub>IN</sub>			2	6	13	ms



## **Performance Characteristics**



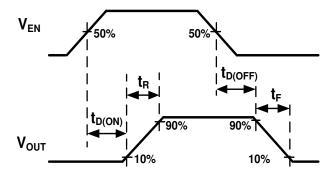
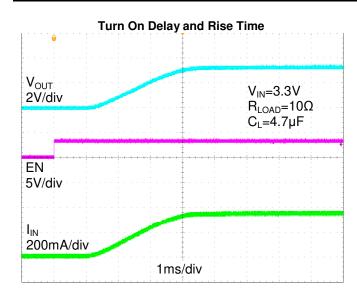
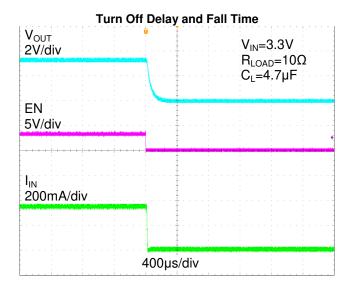


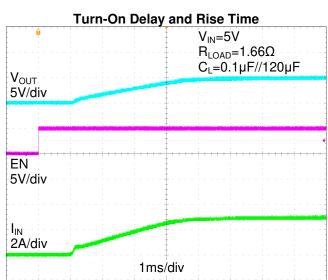
Figure 1. Voltage Waveforms: AP22804B/AP22814B (Active Low, Left), AP22804A/AP22814A (Active High, Right)

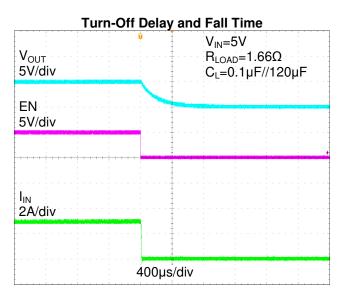


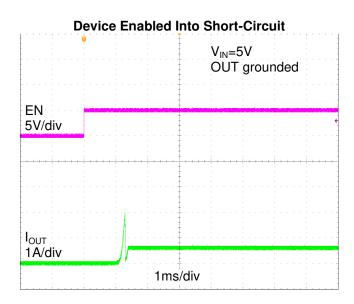
# $\hline \textbf{Performance Characteristics} \ \ (\text{Cont.}) \ \ (T_{A} = +25^{\circ}\text{C}, \ V_{IN} = 5\text{V}, \ C_{IN} = 1\mu\text{F}, \ C_{L} = 0.1\mu\text{F}, \ unless otherwise specified.})$

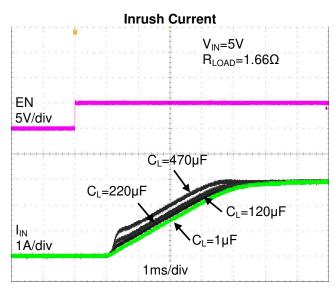








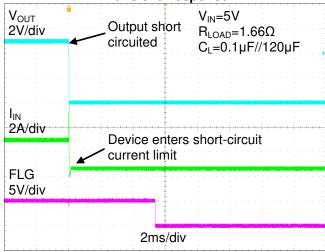




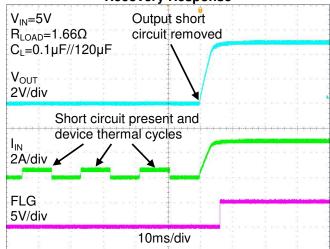


## Performance Characteristics (Cont.) ( $T_A = +25^{\circ}C$ , $V_{IN} = 5V$ , $C_{IN} = 1\mu F$ , $C_L = 0.1\mu F$ , unless otherwise specified.)

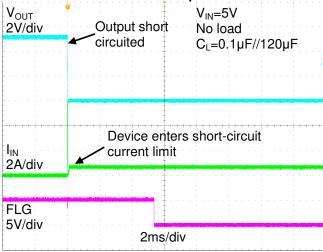
# **Full-Load to Short-Circuit Transient Response** $V_{IN}=5V$



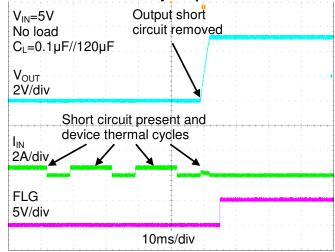
#### Short-Circuit to Full-Load **Recovery Response**



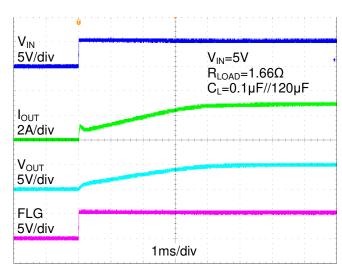
#### No-Load to Short-Circuit **Transient Response**



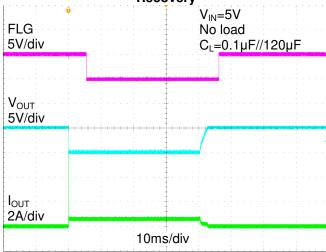
#### **Short-Circuit to No-Load Recovery Response**



#### **Power ON**

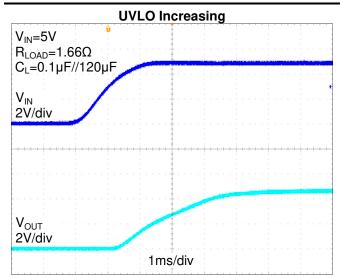


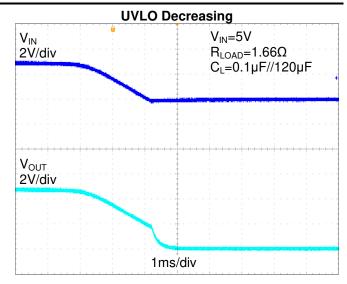
## **Short-Circuit with Blanking Time and** Recovery



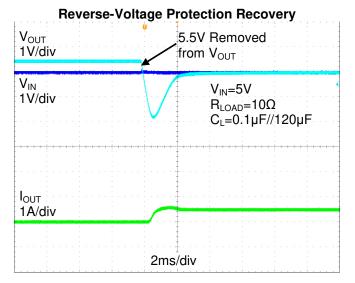


# $\textbf{Performance Characteristics} \ \ (\text{Cont.}) \ \ (T_A = +25^{\circ}\text{C}, \ V_{IN} = 5\text{V}, \ C_{IN} = 1\mu\text{F}, \ C_L = 0.1\mu\text{F}, \ unless otherwise specified.})$





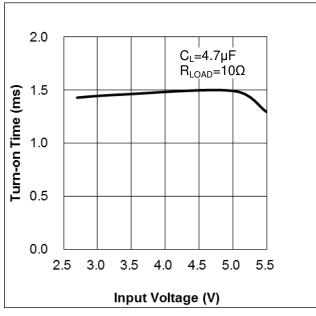
# 



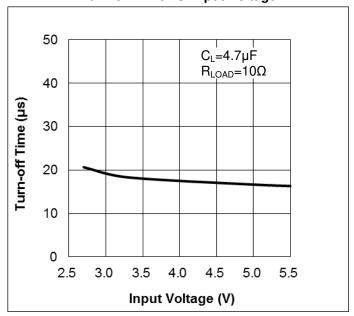


# $\label{eq:cont.} \textbf{Performance Characteristics} \ \ (\text{Cont.}) \ \ (T_A = +25^{\circ}\text{C}, \ V_{IN} = 5\text{V}, \ C_{IN} = 1\mu\text{F}, \ C_L = 0.1\mu\text{F}, \ unless otherwise specified.})$

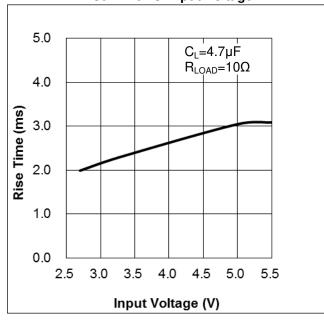
### Turn-on Time vs. Input Voltage



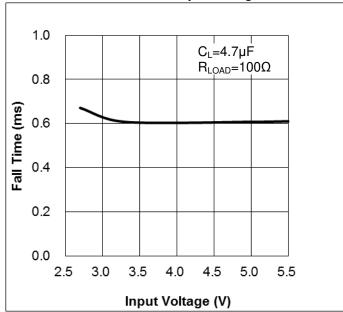
#### Turn-off Time vs. Input Voltage



## Rise Time vs. Input Voltage



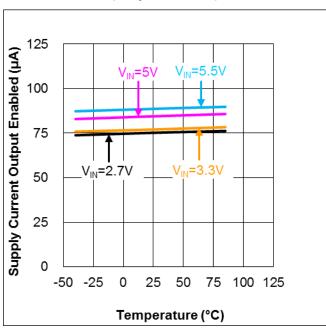
### Fall Time vs. Input Voltage



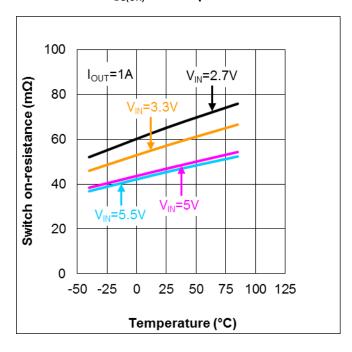


# $\begin{tabular}{ll} \textbf{Performance Characteristics} & (Cont.) & (T_A = +25^{\circ}C, \ V_{IN} = 5V, \ C_{IN} = 1 \mu F, \ C_L = 0.1 \mu F, \ unless otherwise specified.) \\ \end{tabular}$

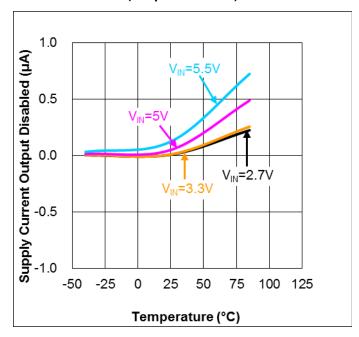
# Supply Current vs. Temperature (Output Enabled)



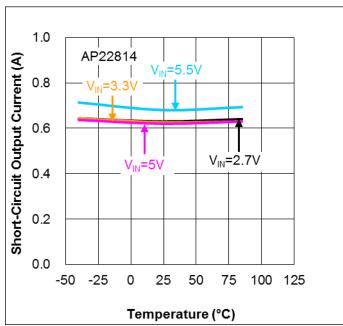
R<sub>DS(ON)</sub> vs. Temperature



# Supply Current vs. Temperature (Output Disabled)



**Short-Circuit Output Current vs. Temperature** 



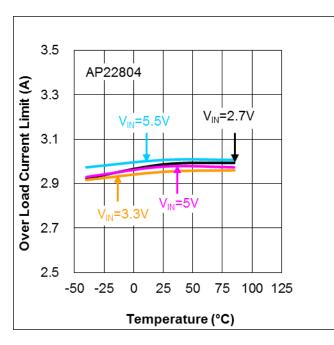


# $\begin{tabular}{ll} \textbf{Performance Characteristics} & (Cont.) & (T_A = +25^{\circ}C, \ V_{IN} = 5V, \ C_{IN} = 1 \mu F, \ C_L = 0.1 \mu F, \ unless otherwise specified.) \\ \end{tabular}$

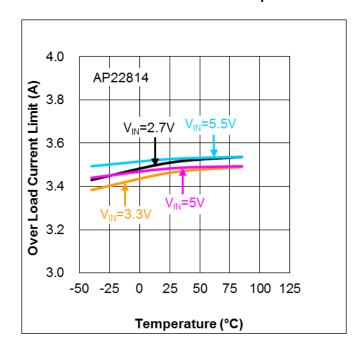
### **Short-Circuit Output Current vs. Temperature**

# 1.0 Short-Circuit Output Current (A) AP22804 8.0 0.6 0.4 V<sub>IN</sub>=2.7V $V_{IN}=3.3V$ 0.2 0.0 -50 -25 0 25 50 75 100 125 Temperature (°C)

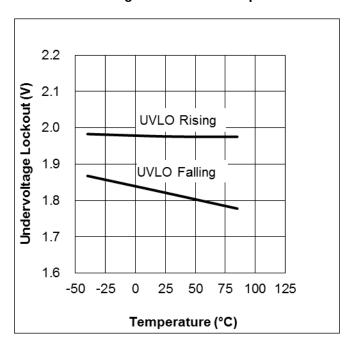
## **Over Load Current Limit vs. Temperature**



#### **Over Load Current Limit vs. Temperature**



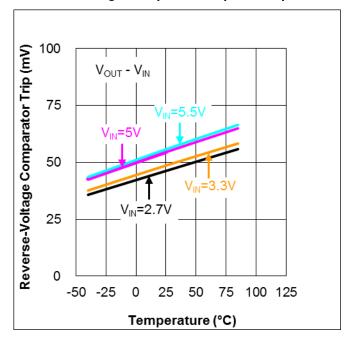
### **Under voltage Lockout vs. Temperature**



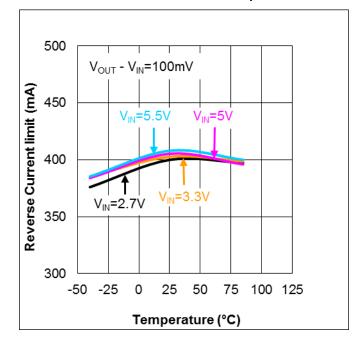


# $\textbf{Performance Characteristics} \ \ (\text{Cont.}) \ \ (T_A = +25^{\circ}\text{C}, \ V_{IN} = 5\text{V}, \ C_{IN} = 1\mu\text{F}, \ C_L = 0.1\mu\text{F}, \ unless otherwise specified.})$

### **Reverse-Voltage Comparator Trip vs Temperature**



### **Reverse Current limit vs Temperature**





## **Application Information**

#### **Input and Output Capacitors**

It is needed to place a  $1\mu$ F X7R or X5R ceramic bypass capacitor between IN and GND, close to the device. Placing a high-value capacitor ( $10\mu$ F or  $47\mu$ F) close to input pin is also recommended when the output transient load is heavy. This precaution reduces power-supply transients that may cause ringing on the input.

Connect a minimum 100µF low ESR electrolytic or tantalum capacitor (or 10µF MLCC) between OUT and GND is also needed for hot-plug applications. It's a must to bypass the output with a 0.1µF ceramic capacitor which improves the immunity of the device to short-circuit transients. The Bulky 100µF or larger capacitors help to reduce output droop voltage when a device is plugged in. When abnormal short-circuit condition happens, these capacitors can also reduce output negative voltage due to parasitic inductive effect and avoid device damage.

Please note without the bypass capacitors, an output short may cause ringing on the input; if the voltage is over the maximum voltage rating, it will destroy the internal control circuitry even the duration is short.

#### **FLG Response**

When an over-current or over-temperature shutdown condition is encountered, the FLG open-drain output goes active low after a nominal 6ms deglitch timeout. The FLG output remains low until both over-current and over-temperature conditions are removed. Connecting a heavy capacitive load to the output of the device can cause a momentary over-current condition, which does not trigger the FLG due to the 6ms deglitch timeout. The AP22804/AP22814 is designed to eliminate false over-current reporting without the need of external components to remove unwanted pulses.

#### **Over-Current and Short Circuit Protection**

An internal sensing FET is employed to check for over-current conditions. Unlike current-sense resistors, sense FETs do not increase the series resistance of the current path. When an overcurrent condition is detected, the device maintains a constant output current and reduces the output voltage accordingly. Complete shutdown occurs only if the fault stays long enough to activate thermal limiting.

Three possible overload conditions can occur. In the first condition, the output has been shorted to GND before the device is enabled or before  $V_{IN}$  has been applied. The AP22804/AP22814 senses the short circuit and immediately clamps output current to a certain safe level.

In the second condition, an output short or an overload occurs while the device is enabled. At the instance the overload occurs, higher current may flow for a very short period of time before the current limit function can react. After the current limit function has tripped, the device switches into current limiting mode and the current is clamped at I<sub>LIMIT</sub>, or I<sub>SHORT</sub>.

In the third condition, the load has been gradually increased beyond the recommended operating current. The current is permitted to rise until the current-limit threshold (I<sub>TRIG</sub>) is reached or until the thermal limit of the device is exceeded. The AP22804/AP22814 is capable of delivering current up to the current-limit threshold without damaging the device. Once the threshold has been reached, the device switches into its current limiting mode and is set at I<sub>LIMIT</sub>.

#### **Thermal Protection**

Thermal protection prevents the IC from damage when heavy-overload or short-circuit faults are present for extended periods of time. The AP22804/AP22814 implements a thermal sensing to monitor the operating junction temperature of the power distribution switch. Once the die temperature rises to approximately +140°C due to excessive power dissipation in an over-current or short-circuit condition the internal thermal sense circuitry turns the power switch off, thus preventing the power switch from damage. Hysteresis is built into the thermal sense circuit allowing the device to cool down approximately +35°C before the switch turns back on. The switch continues to cycle in this manner until the load fault or input power is removed. The FLG open-drain output is asserted when an over-temperature shutdown or over-current occurs with 6ms deglitch.

#### **ON/OFF Input Operator**

The EN input allows the output current to be switched on and off using a GPIO compatible input. The high signal (switch on) should be at least 1.5V, and the low signal (switch off) no higher than 0.65V. This pin should NOT be left floating. It is advisable to hold the EN signal low when applying or removing power.

#### **Under-voltage Lockout (UVLO)**

Under-voltage lockout function (UVLO) keeps the internal power switch from being turned on until the power supply has reached at least 2V, even if the switch is enabled. Whenever the input voltage falls below approximately 2V, the power switch is quickly turned off. This facilitates the design of hot-insertion systems where it is not possible to turn off the power switch before input power is removed.



## **Application Information (Cont.)**

#### **Discharge Function**

The discharge function of the device is active when enable is disabled or de-asserted. The discharge function with the N-MOS power switch implementation is activated and offers a resistive discharge path for the external storage capacitor. This is designed for discharging any residue of the output voltage when either no external output resistance or load resistance is present at the output.

#### **Output Reverse-Voltage / Current Protection**

The output reverse-voltage protection turns off the MOSFET switch whenever the output voltage is higher than the input voltage by 50mV for 6ms and the MOSFET switch will turn on when output reverse-voltage/current conditions is removed.

#### **Power Dissipation and Junction Temperature**

The low on-resistance of the internal MOSFET allows the small surface-mount packages to pass large current. Using the maximum operating ambient temperature (T<sub>A</sub>) and R<sub>DS(ON)</sub>, the power dissipation can be calculated by:

$$P_D = R_{DS(ON)} \times I^2$$

Finally, calculate the junction temperature:

$$T_J = P_D \times R_{\theta JA} + T_A$$

Where:

T<sub>A</sub> = Ambient temperature °C

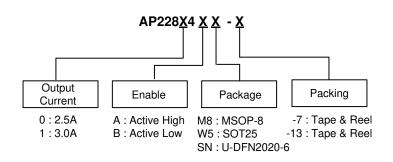
 $R_{\theta JA}$  = Thermal resistance

P<sub>D</sub> = Total power dissipation

#### **Board Layout Instruction**

Placing input and output capacitors,  $1\mu\text{F}$  and  $0.1\mu\text{F}+100\mu\text{F}$  respectively, close and next to the device pins must be implemented to minimize the effects of parasitic inductance. For best performance, all trace lengths should be kept as short as possible. The input and output PCB traces should be as wide as possible. Use a ground plane to enhance the power dissipation capability of the device.

## **Ordering Information**

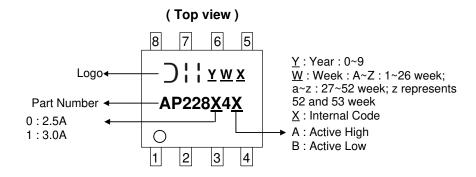


Port Number	Part Number Package Code Packaging		7"/13" Tape and Reel		
Part Number			Quantity	Part Number Suffix	
AP228X4AM8-13	M8	MSOP-8	2500/Tape & Reel	-13	
AP228X4AW5-7	W5	SOT25	3000/Tape & Reel	-7	
AP228X4ASN-7	SN	U-DFN2020-6	3000/Tape & Reel	-7	
AP228X4BM8-13	M8	MSOP-8	2500/Tape & Reel	-13	
AP228X4BW5-7	W5	SOT25	3000/Tape & Reel	-7	
AP228X4BSN-7	SN	U-DFN2020-6	3000/Tape & Reel	-7	



## **Marking Information**

#### (1) MSOP-8



(2) SOT25

### (Top View)

5 4

XXYWX

XX: Identification code

Y: Year 0~9

 $\underline{W}$  : Week : A~Z : 1~26 week;

a~z: 27~52 week; z represents

52 and 53 week  $\underline{X}$ : A~Z: Green

1 2 3

Part Number	Package Type	Identification Code
AP22804AW5-7	SOT25	2Y
AP22804BW5-7	SOT25	2Z
AP22814AW5-7	SOT25	7Y
AP22814BW5-7	SOT25	7Z

(3) U-DFN2020-6

## (Top View)

XX YWX XX: Identification Code

Y: Year: 0~9

W: Week: A~Z: 1~26 week; a~z: 27~52 week; z represents

52 and 53 week

X : Internal Code

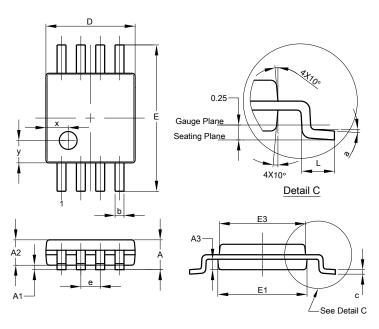
Part Number	Package Type	Identification Code
AP22804ASN-7	U-DFN2020-6	2Y
AP22804BSN-7	U-DFN2020-6	2Z
AP22814ASN-7	U-DFN2020-6	7Y
AP22814BSN-7	U-DFN2020-6	7Z



# **Package Outline Dimensions**

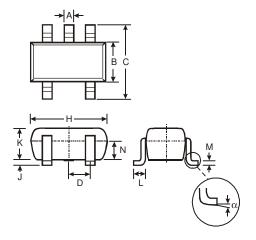
 $Please\ see\ http://www.diodes.com/package-outlines.html\ for\ the\ latest\ version.$ 

## (1) MSOP-8



	MSOP-8				
Dim	Min	Max	Тур		
Α	-	1.10	-		
A1	0.05	0.15	0.10		
A2	0.75	0.95	0.86		
A3	0.29	0.49	0.39		
b	0.22	0.38	0.30		
С	0.08	0.23	0.15		
D	2.90	3.10	3.00		
Ε	4.70	5.10	4.90		
E1	2.90	3.10	3.00		
E3	2.85	3.05	2.95		
е	-	-	0.65		
L	0.40	0.80	0.60		
а	0°	8°	4°		
Х	-	-	0.750		
у	-	-	0.750		
AII [	Dimen	sions	in mm		

### (2) SOT25



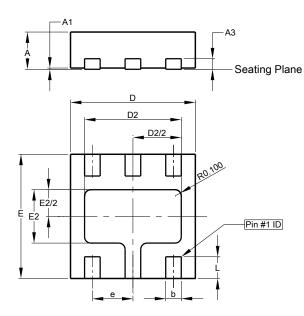
SOT25						
Dim	Min	Max	Тур			
Α	0.35	0.50	0.38			
В	1.50	1.70	1.60			
C	2.70	3.00	2.80			
D	-	-	0.95			
H	2.90	3.10	3.00			
۲	0.013	0.10	0.05			
K	1.00	1.30	1.10			
L	0.35	0.55	0.40			
М	0.10	0.20	0.15			
N	0.70	0.80	0.75			
α	0°	8°	-			
All D	All Dimensions in mm					



## Package Outline Dimensions (Cont.)

Please see http://www.diodes.com/package-outlines.html for the latest version.

### (3) U-DFN2020-6

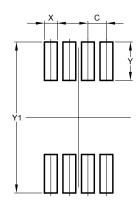


	U-DFN2020-6						
Dim	Min	Max	Тур				
Α	0.57	0.63	0.60				
<b>A</b> 1	0	0.05	0.03				
A3	-	-	0.15				
b	0.20	0.30	0.25				
D	1.95	2.075	2.00				
D2	1.45	1.65	1.55				
е	1	-	0.65				
E	1.95	2.075	2.00				
E2	0.76	0.96	0.86				
L	0.30	0.40	0.35				
All D	imens	ions in	mm				

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### (1) MSOP-8



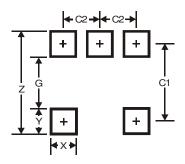
Dimensions	Value (in mm)
С	0.650
Х	0.450
Υ	1.350
V1	5.300



# Suggested Pad Layout (Cont.)

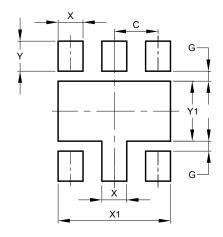
Please see http://www.diodes.com/package-outlines.html for the latest version.

### (2) SOT25



Dimensions	Value
Z	3.20
G	1.60
Х	0.55
Υ	0.80
C1	2.40
C2	0.95

### (3) U-DFN2020-6



Dimensions	Value
	(in mm)
С	0.65
G	0.15
Х	0.37
X1	1.67
Y	0.45
V1	0.90



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